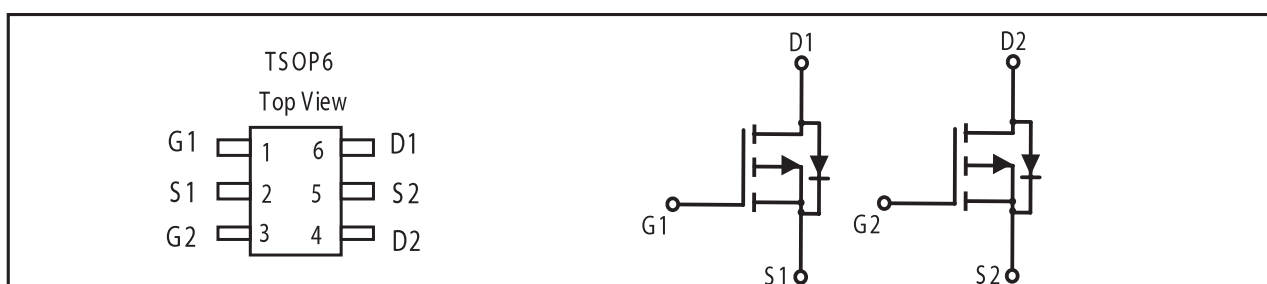


PRODUCT SUMMARY

V_{DS}	I_D	$R_{DS(ON)} (m\Omega) MAX$
-20V	-2A	130 @ $V_{GS} = -4.5V$
		190 @ $V_{GS} = -2.5V$

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- SOT-26 Package.

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous ^a @ $T_C=25^\circ C$ -Pulsed ^b	I_D	-2	A
	I_{DM}	-7	A
Drain-Source Diode Forward Current ^a	I_S	-1.25	A
Maximum Power Dissipation ^a	P_D	1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	$R_{\theta JA}$	125	$^\circ C/W$
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